MMBT3906LT1H

General Purpose Transistor

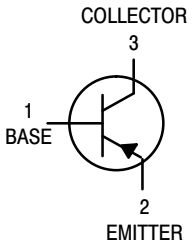
PNP Silicon

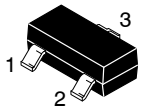
Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

www.onsemi.com





SOT−23 (TO−236)
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−40	Vdc
Collector − Base Voltage	V_{CBO}	−40	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−200	mAdc
Collector Current − Peak (Note 3)	I_{CM}	−800	mAdc

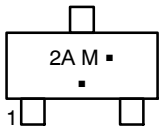
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR− 5 Board (Note 1) @ T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
3. Reference SOA curve.

MARKING DIAGRAM



2A = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906LT1H	SOT−23 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = −1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	−40	–	Vdc
Collector – Base Breakdown Voltage (I_C = −10 μAdc, I_E = 0)	$V_{(BR)CBO}$	−40	–	Vdc
Emitter – Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	–	Vdc
Base Cutoff Current (V_{CE} = −30 Vdc, V_{EB} = −3.0 Vdc)	I_{BL}	–	−50	nAdc
Collector Cutoff Current (V_{CE} = −30 Vdc, V_{EB} = −3.0 Vdc)	I_{CEX}	–	−50	nAdc
ON CHARACTERISTICS (Note 4)				
DC Current Gain (I_C = −0.1 mAdc, V_{CE} = −1.0 Vdc) (I_C = −1.0 mAdc, V_{CE} = −1.0 Vdc) (I_C = −10 mAdc, V_{CE} = −1.0 Vdc) (I_C = −50 mAdc, V_{CE} = −1.0 Vdc) (I_C = −100 mAdc, V_{CE} = −1.0 Vdc)	H_{FE}	 60 80 100 60 30	 – – 300 – –	–
Collector – Emitter Saturation Voltage (I_C = −10 mAdc, I_B = −1.0 mAdc) (I_C = −50 mAdc, I_B = −5.0 mAdc)	$V_{CE(sat)}$	 – –	 −0.25 −0.4	Vdc
Base – Emitter Saturation Voltage (I_C = −10 mAdc, I_B = −1.0 mAdc) (I_C = −50 mAdc, I_B = −5.0 mAdc)	$V_{BE(sat)}$	 −0.65 –	 −0.85 −0.95	Vdc
SMALL– SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I_C = −10 mAdc, V_{CE} = −20 Vdc, f = 100 MHz)	f_T	250	–	MHz
Output Capacitance (V_{CB} = −5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	4.5	pF
Input Capacitance (V_{EB} = −0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	10	pF
Input Impedance (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{re}	0.1	10	X 10^{-4}
Small – Signal Current Gain (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{fe}	100	400	–
Output Admittance (I_C = −1.0 mAdc, V_{CE} = −10 Vdc, f = 1.0 kHz)	h_{oe}	3.0	60	μmhos
Noise Figure (I_C = −100 μAdc, V_{CE} = −5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB
SWITCHING CHARACTERISTICS				
Delay Time	(V_{CC} = −3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = −10 mAdc, I_{B1} = −1.0 mAdc) t_d	–	35	ns
Rise Time	t_r	–	35	
Storage Time	(V_{CC} = −3.0 Vdc, I_C = −10 mAdc, I_{B1} = I_{B2} = −1.0 mAdc) t_s	–	225	ns
Fall Time	t_f	–	75	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

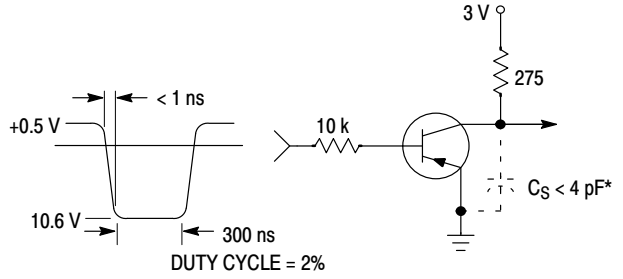


Figure 1. Delay and Rise Time Equivalent Test Circuit

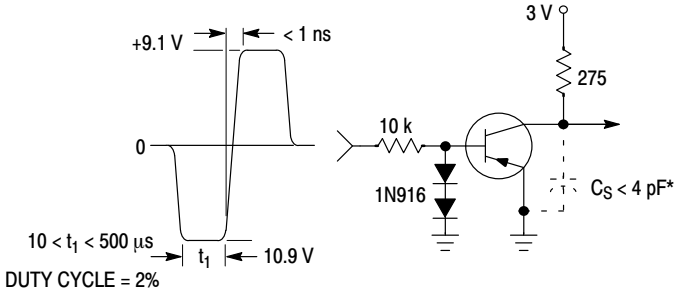


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

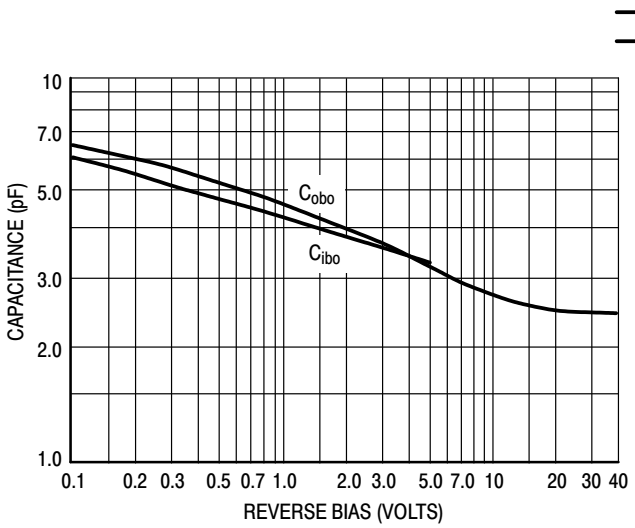


Figure 3. Capacitance

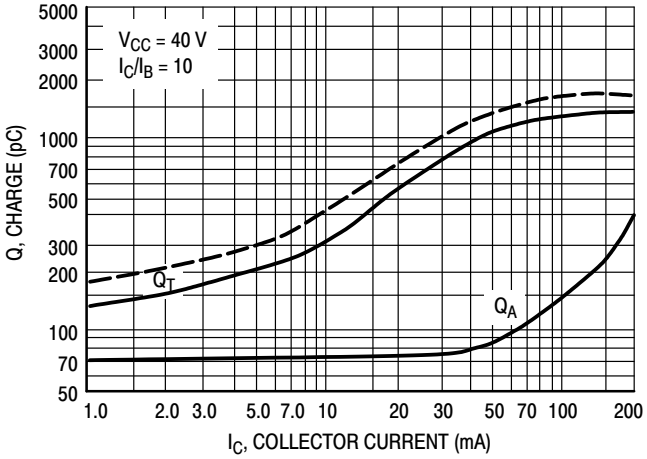


Figure 4. Charge Data

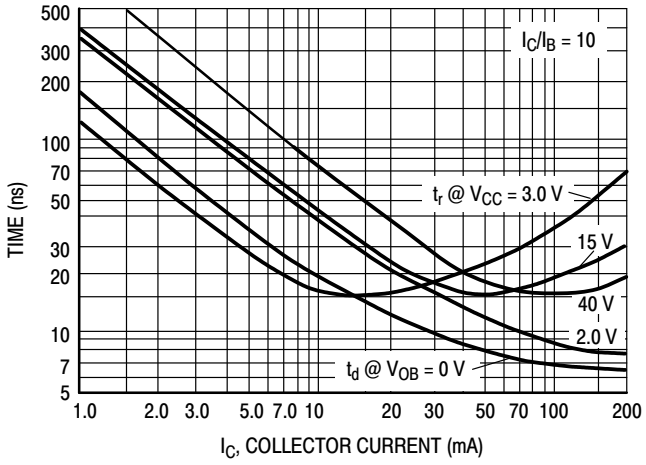


Figure 5. Turn – On Time

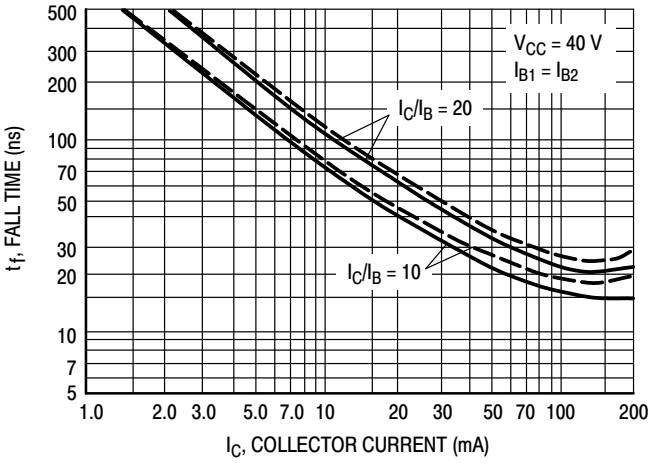


Figure 6. Fall Time

TYPICAL AUDIO SMALL−SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = −5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

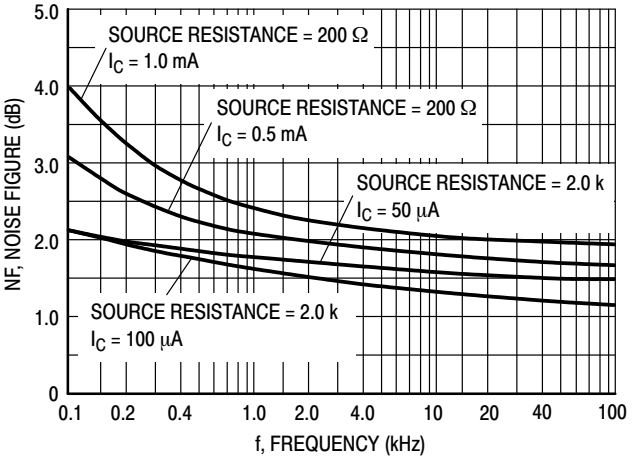


Figure 7.

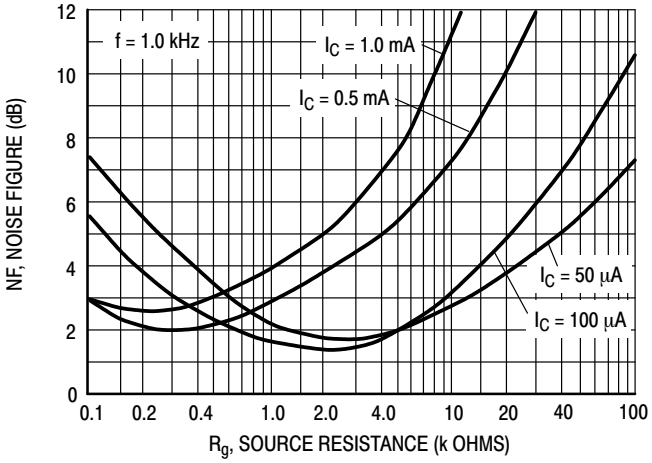


Figure 8.

h PARAMETERS

(V_{CE} = −10 Vdc, f = 1.0 kHz, T_A = 25°C)

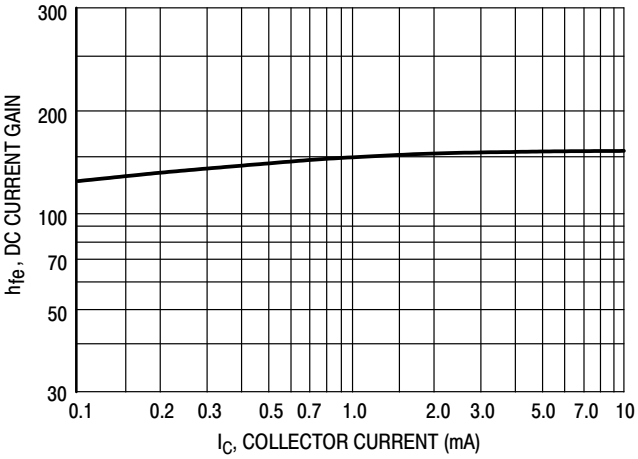


Figure 9. Current Gain

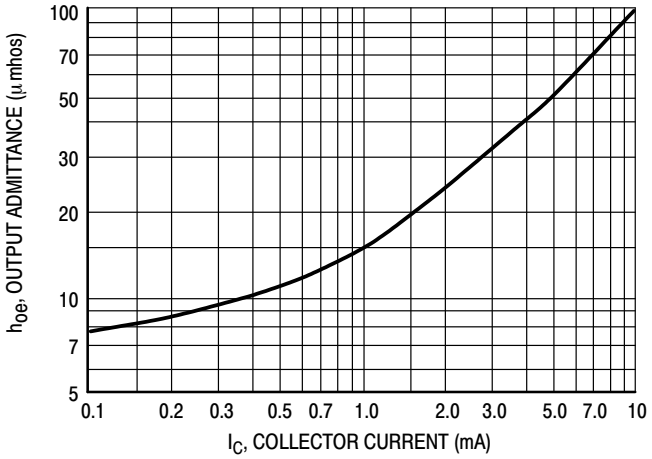


Figure 10. Output Admittance

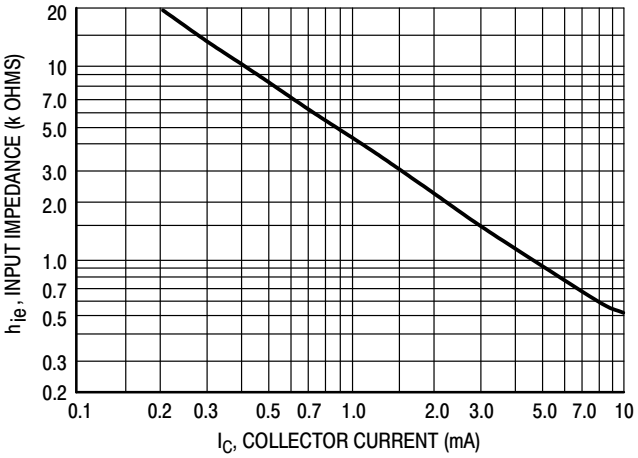


Figure 11. Input Impedance

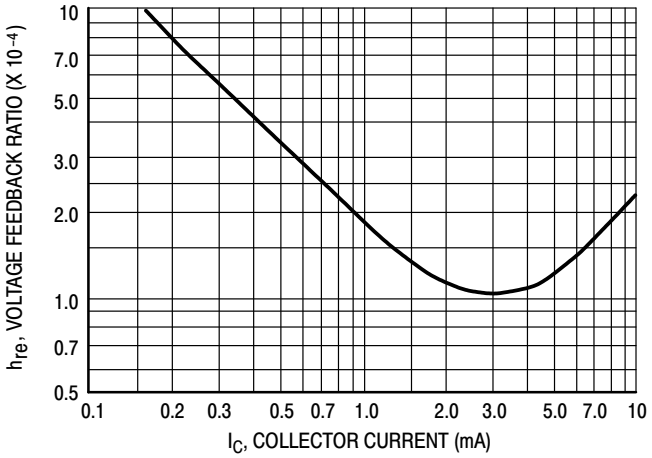


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

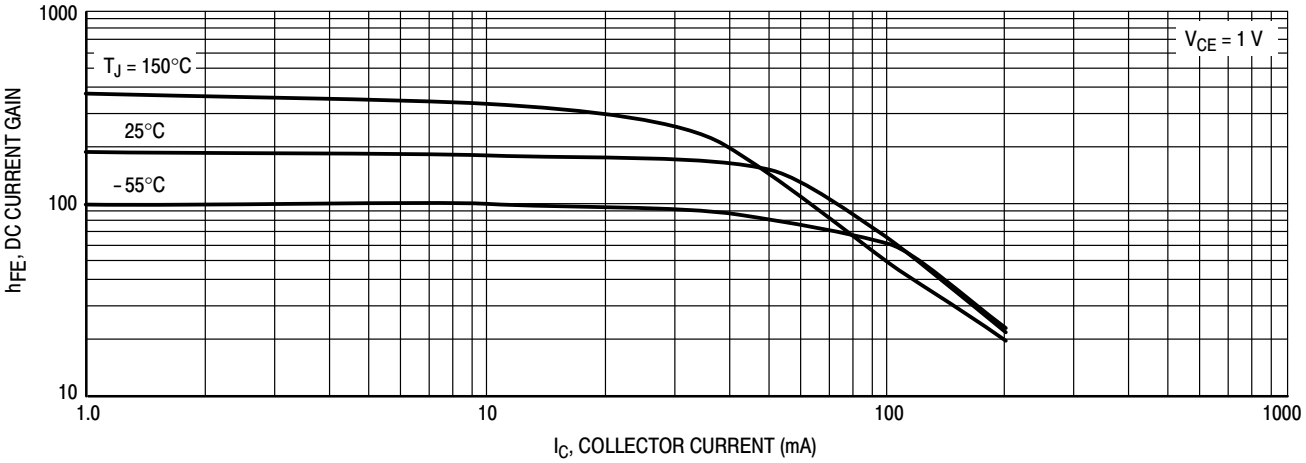


Figure 13. DC Current Gain

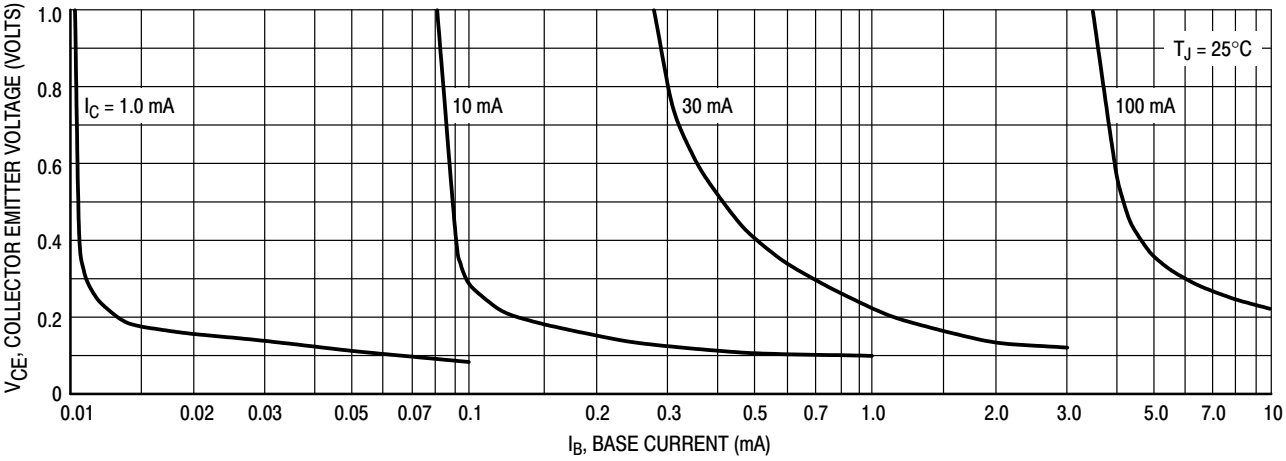


Figure 14. Collector Saturation Region

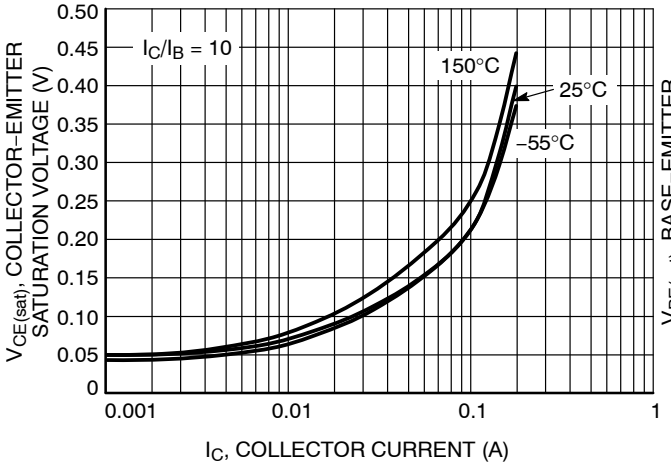


Figure 15. Collector Emitter Saturation Voltage vs. Collector Current

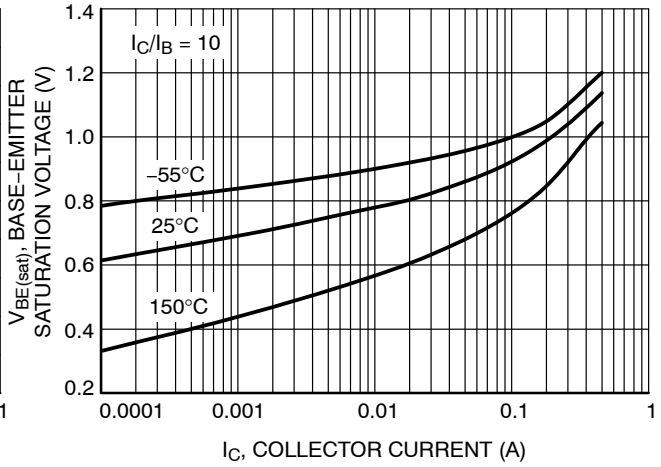


Figure 16. Base Emitter Saturation Voltage vs. Collector Current

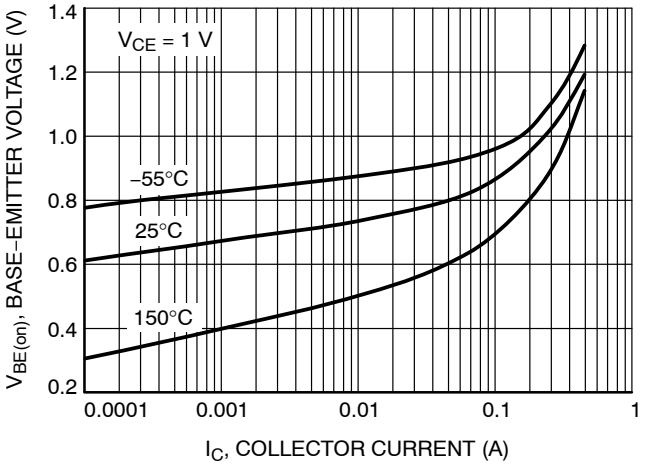


Figure 17. Base Emitter Voltage vs. Collector Current

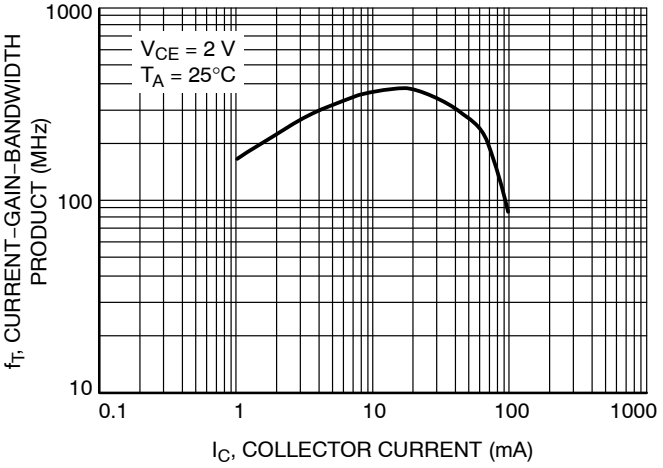


Figure 18. Current Gain Bandwidth vs. Collector Current

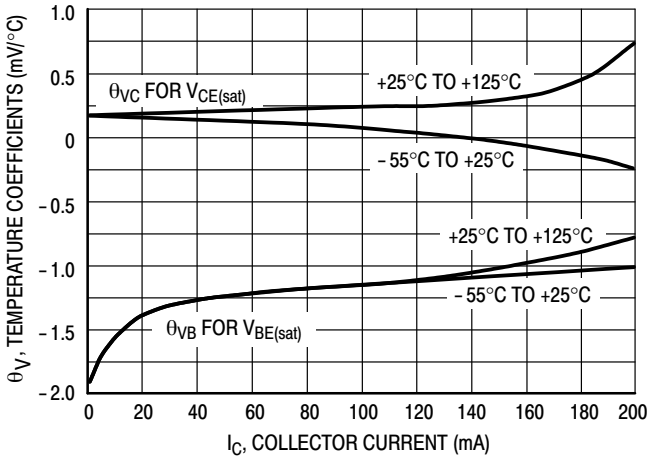


Figure 19. Temperature Coefficients

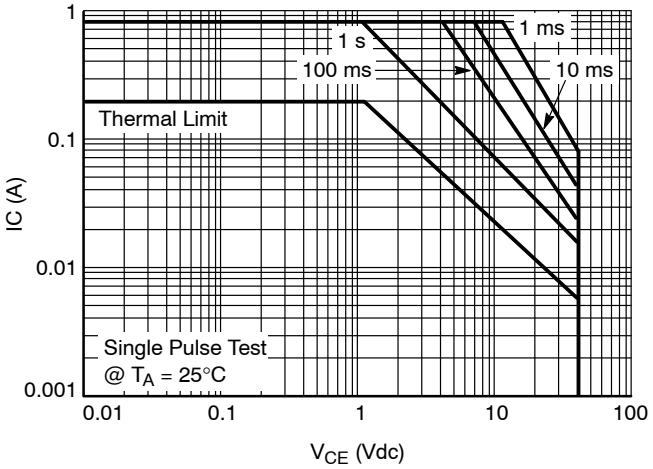
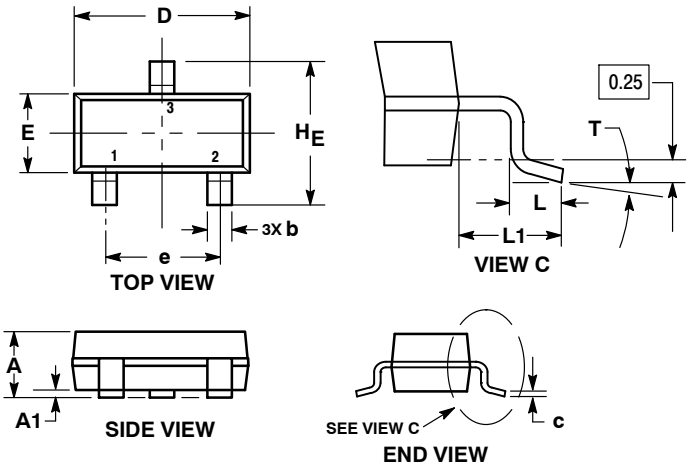


Figure 20. Safe Operating Area

MMBT3906LT1H

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

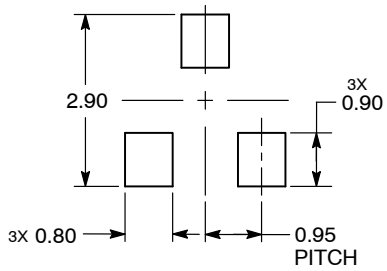


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10 °	0 °	−−−	10 °

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative